## Symmetrical Gate Turn-Off Thyristor Type SA30AP1000F0



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## **Absolute Maximum Ratings**

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>DRM</sub>	Repetitive peak off-state voltage, (note 1)	3000	V
$V_{RSM}$	Non-repetitive peak off-state voltage, (note 1)	3100	V
$V_{RRM}$	Repetitive peak reverse voltage	3000	V
$V_{RSM}$	Non-repetitive peak reverse voltage	3000	V
note 1)	$V_{GK} = -2V$		

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I <sub>TGQ</sub>	Peak turn-off current (note 1)	1000	А
L <sub>S</sub>	Snubber loop impedance, $I_{TM} = I_{TGQ}$ (note 1)	0.3	μΗ
$I_{T(AV)M}$	Mean on-state current, T <sub>sink</sub> = 55°C, (note 2)	600	А
I <sub>T(RMS)</sub>	Nominal RMS on-state current, T <sub>sink</sub> = 25°C (note 2)	1180	А
I <sub>TSM</sub>	Peak non-repetitive surge current t <sub>p</sub> = 10ms	10.0	kA
I <sub>TSM2</sub>	Peak non-repetitive surge current (note 3)	18.0	kA
I <sup>2</sup> t	$I^2$ t capacity for fusing $t_p = 10$ ms	500 · 10 <sup>3</sup>	$A^2s$
(di/dt) <sub>cr</sub>	Critical rate of rise of on-state current, (note 4)	1000	A/µs
P <sub>FGM</sub>	Peak forward gate power	200	W
$P_{RGM}$	Peark reverse gate power	8	kW
I <sub>FGM</sub>	Peak forward gate current	140	А
$V_{RGM}$	Peak reverse gate voltage (note 5)	18	V
t <sub>off</sub>	Minimum permissible off-time, $I_{TM} = I_{TGQ}$ (note 1)	130	μs
t <sub>on</sub>	Minimum permissible off-time	20	μs
T <sub>jop</sub>	Operating temperature range	-40 to +125	°C
$T_{\text{stg}}$	Storage temperature range	-40 to +150	°C
note 1)	$T_j$ = 125°C, $V_D$ = 80% $V_{DM}$ , $V_{DM} \le V_{DRM}$ , $di_{GQ}/dt$ = 20A/ $\mu$ s, $I_{TM}$ = $I_{TGQ}$ and $C_S$ = 1000 $I_{TM}$	= 2μF	
note 2)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Half-sinewave, t <sub>p</sub> = 2ms		
note 4)	For di/dt > 1000A/µs please consult factory.		
note 5)	May exceed this value during turn-off avalanche period.		



### **Characteristics**

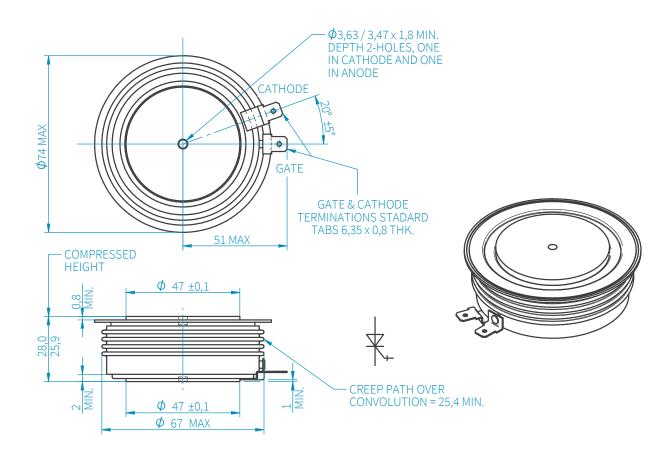
	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
$V_{TM}$	Maximum peak on-state voltage	I <sub>G</sub> = 2A, I <sub>T</sub> = 1200A	-	3	3.5	V
IL	Latching current	T 25°C	-	10	-	А
I <sub>H</sub>	Holding current	T <sub>j</sub> = 25°C	-	10	-	А
(dv/dt) <sub>cr</sub>	Critical rate of rise of off-state voltage $V_D = 80\%V_{DRM}$ , $V_{GR} = -2V$		1000	-	-	V/µs
I <sub>DRM</sub>	Peak off-state current	Rated $V_{DRM}$ , $V_{GR} = -2V$	-	-	50	mA
I <sub>RRM</sub>	Peak reverse current	Rated V <sub>RRM</sub>	-	-	100	mA
$I_{GKM}$	Peak negative gate leakage current	$V_{GR} = -16V$	-	-	200	mA
		$T_j = -40$ °C, $V_D = 25$ V, $R_L = 25$ m $\Omega$	-	1.0	-	V
$V_{GT}$	Gate trigger voltage	$T_j = 25^{\circ}\text{C}, V_D = 25\text{V}, R_L = 25\text{m}\Omega$	-	0.9	-	V
		$T_j = 125$ °C, $V_D = 25V$ , $R_L = 25m\Omega$	-	0.8	-	V
		$T_j = -40$ °C, $V_D = 25$ V, $R_L = 25$ m $\Omega$	-	2	7	А
$I_{GT}$	Gate trigger current	$T_j = 25^{\circ}\text{C}, V_D = 25\text{V}, R_L = 25\text{m}\Omega$	-	0.5	2	А
		$T_j = 125$ °C, $V_D = 25$ V, $R_L = 25$ m $\Omega$	-	50	300	mA
t <sub>d</sub>	Delay time	(note 2)	-	2	-	μs
t <sub>gt</sub>	Turn-on time	Conditions as for $t_d$ , (10% $I_{GM}$ to 10% $V_D$ )	-	5	8	μs
t <sub>f</sub>	Fall time	(note 3)	-	1	-	μs
t <sub>gq</sub>	Turn-off time	Conditions as for $t_f$ , (10% $I_{GQ}$ to 10% $I_{TGQ}$ )	-	19	21	μs
$I_{GQ}$	Turn-off gate current	Conditions as for t <sub>f</sub>	-	260	-	А
$Q_{GQ}$	Turn-off gate charge	Conditions as for t	-	3000	4000	mC
t <sub>tail</sub>	Tail time	Conditions as for $t_f$ , (10% $I_{TGQ}$ to $I_{TGQ}$ < 1A)	-	70	95	μs
t <sub>gw</sub>	Gate off-time (note 4)	Conditions as for t <sub>f</sub>	280	-	-	μs
		Double side cooled	-	-	0.027	K/W
$R_{thJK}$	Thermal resistance, junction to sink	Cathode side cooled	-	-	0.070	K/W
		Anode side cooled	-	-	0.045	K/W
F	Mounting force	(note 5)	15	-	25	kN
W <sub>t</sub>	Weight		-	480	-	g
note 1)	Unless otherwise indicated T <sub>j</sub> = 125°C					
note 2)	$V_D = 50\% V_{DRM}$ , $I_{TGQ} = 1000A$ , $I_{GM} = 20A$ , $di_G/dt = 10A/\mu s$ , $T_j = 25^{\circ}C$ , $di/dt = 300A/\mu s$ , $(10\% I_{GM} to 90\% V_D)$					
note 3)	$V_D = 80\% V_{DRM}$ , $I_{TGQ} = 1000A$ , $C_S = 2\mu F$ , $di_G/dt = 20A/\mu s$ , $V_{GR} = -16V$ , $(90\% I_{TGQ})$					
note 4)	The gate off-time is the period during which the gate circuit is required to remain low impedance to allow for the passage of tail current.					
note 5)	For other clamping forces, consult factory.					

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